

Amendments to the Specification:

Please replace the paragraph beginning at page 1, line 11 with the following amended paragraph:

-- Silicon carbide (hereinafter abbreviated as SiC), having a wide band gap and a maximum insulation field larger by about one digit as compared with silicon (hereinafter abbreviated as Si), is a material expected for application to next-generation power semiconductor devices. SiC has heretofore been applied to various electronic devices through single-crystalline wafers referred to as 4H-SiC or 6H-SiC, and is regarded as suitable to high-temperature/high-power devices in particular. The aforementioned crystal is alpha-phase SiC formed by stacking zinc blende and wurtzite. Semiconductor devices have also been experimentally manufactured through a beta-phase SiC crystal referred to as 3C-SiC. A Schottky diode, a MOSFET (metal oxide semiconductor field-effect transistor), thyristor etc. serving as power devices or a CMOS (complementary ~~metal~~ metal-oxide semiconductor)-IC (integrated circuit), which is the most versatile semiconductor device, has recently been experimentally manufactured, and it has been confirmed from the characteristics thereof that the characteristics are extremely excellent as compared with conventional Si semiconductor devices. --